

TC74VHC03F, TC74VHC03FN, TC74VHC03FT

QUAD 2-INPUT NAND GATE (OPEN DRAIN)

The TC74VHC03 is an advanced high speed CMOS 2-INPUT NAND GATE fabricated with silicon gate C²MOS technology. It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

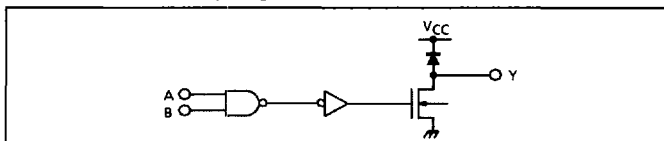
Pin configuration and function are the same as the TC74VHC00. But the TC74VHC03 has, as its outputs, high performance MOS N-channel transistors. (OPEN-DRAIN outputs) This device can, therefore, with a suitable pull-up resistors, be used in wired-AND, LED driver and other application.

An input protection circuit ensures that 0 to 7V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5V to 3V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

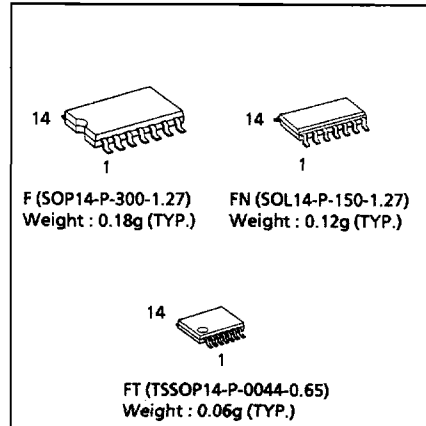
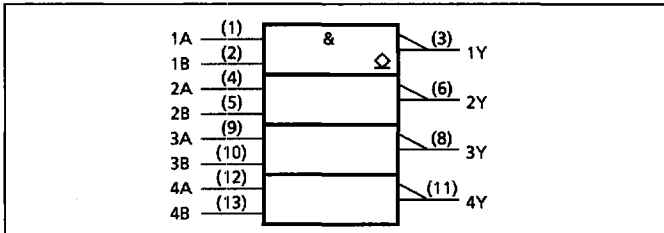
FEATURES :

- High Speed..... $t_{pZ} = 3.7ns$ (typ.) at $V_{CC} = 5V$
- Low Power Dissipation..... $I_{CC} = 2\mu A$ (Max.) at $T_a = 25^\circ C$
- High Noise Immunity..... $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (Min.)
- Power Down Protection is provided on all inputs.
- Wide Operating Voltage Range..... $V_{CC} (opr) = 2V \sim 5.5V$
- Low Noise $V_{OLP} = 0.8V$ (Max.)
- Pin and Function Compatible with 74ALS03

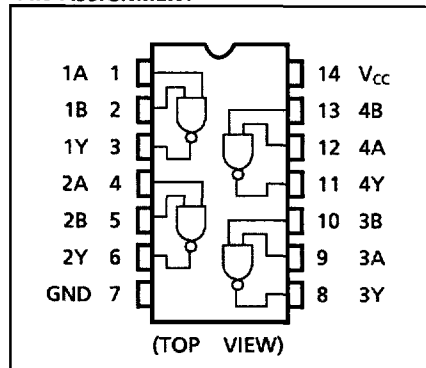
SYSTEM DIAGRAM (per gate)



IEC LOGIC SYMBOL



PIN ASSIGNMENT



TRUTH TABLE

A	B	Y
L	L	Z
L	H	Z
H	L	Z
H	H	L

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ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V _{CC}	-0.5~7.0	V
DC Input Voltage	V _{IN}	-0.5~7.0	V
DC Output Voltage	V _{OUT}	-0.5~V _{CC} +0.5	V
Input Diode Current	I _{IK}	-20	mA
Output Diode Current	I _{OK}	±20	mA
DC Output Current	I _{OUT}	25	mA
DC V _{CC} /Ground Current	I _{CC}	±50	mA
Power Dissipation	P _D	180	mW
Storage Temperature	T _{stg}	-65~150	°C

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V _{CC}	2.0~5.5	V
Input Voltage	V _{IN}	0~5.5	V
Output Voltage	V _{OUT}	0~V _{CC}	V
Operating Temperature	T _{opr}	-40~85	°C
Input Rise and Fall Time	dt / dv	0~100 (V _{CC} = 3.3 ± 0.3V) 0~20 (V _{CC} = 5 ± 0.5V)	ns / V

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	V _{CC} (V)	Ta = 25°C			Ta = -40~85°C		UNIT	
				MIN.	TYP.	MAX.	MIN.	MAX.		
High - Level Input Voltage	V _{IH}		2.0 3.0~ 5.5	1.50 V _{CC} × 0.7	— —	— —	1.50 V _{CC} × 0.7	— —	V	
Low - Level Input Voltage	V _{IL}		2.0 3.0~ 5.5	— —	— —	0.50 V _{CC} × 0.3	— —	0.50 V _{CC} × 0.3	V	
Low - Level Output Voltage	V _{OL}	V _{IN} = V _{IH}	I _{OL} = 50μA	2.0	—	0.0	—	0.1	—	0.1
				3.0	—	0.0	—	0.1	—	0.1
				4.5	—	0.0	—	0.1	—	0.1
Output Off-State Current	I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = V _{CC} or GND	5.5	—	—	±0.25	—	±2.50	μA	
				3.0	—	—	—	0.44		
				4.5	—	—	—	0.44		
Input Leakage Current	I _{IN}	V _{IN} = 5.5V or GND	0~5.5	—	—	±0.1	—	±1.0	μA	
Quiescent Supply Current	I _{CC}	V _{IN} = V _{CC} or GND	5.5	—	—	2.0	—	20.0		

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AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3ns$)

PARAMETER	SYMBOL	TEST CONDITION	Ta = 25°C			Ta = -40~85°C		UNIT		
			V _{CC} (V)	C _L (pF)	MIN.	TYP.	MAX.		MIN.	MAX.
Propagation Delay Time	t _{pZL}	R _L = 1kΩ	3.3 ± 0.3	15	—	5.5	7.9	1.0	9.5	ns
				50	—	8.0	11.4	1.0	13.0	
			5.0 ± 0.5	15	—	3.7	5.5	1.0	6.5	
				50	—	5.2	7.5	1.0	8.5	
Propagation Delay Time	t _{pLZ}	R _L = 1kΩ	3.3 ± 0.3	50	—	8.0	11.4	1.0	13.0	ns
			5.0 ± 0.5	50	—	5.2	7.5	1.0	8.5	
Input Capacitance	C _{IN}				—	4	10	—	10	pF
Output Capacitance	C _{OUT}				—	5	—	—	—	pF
Power Dissipation Capacitance	C _{PD}	(Note 1)			—	6	—	—	—	pF

Note (1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC(opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 4 \text{ (per Gate)}$$

NOISE CHARACTERISTICS (Input $t_r = t_f = 3ns$)

PARAMETER	SYMBOL	TEST CONDITION	Ta = 25°C			UNIT
			V _{CC} (V)	TYP.	LIMIT	
Quiet Output Maximum Dynamic V _{OL}	V _{OLP}	C _L = 50pF	5.0	0.3	0.8	V
Quiet Output Minimum Dynamic V _{OL}	V _{OLV}	C _L = 50pF	5.0	-0.3	-0.8	V
Minimum High Level Dynamic Input Voltage	V _{IHD}	C _L = 50pF	5.0	—	3.5	V
Maximum Low Level Dynamic Input Voltage	V _{ILD}	C _L = 50pF	5.0	—	1.5	V

INPUT EQUIVALENT CIRCUIT

